

AMENDMENT TO THE CLAIMS:

1. (Cancelled)
2. (Currently Amended) A reflective liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:
a display electrode made of a reflective material for reflecting the incident light on a surface thereof;
a back-surface electrode disposed in contact with a back surface of the display electrode; and
a transistor for controlling current to the display electrode, said back-surface electrode and the transistor being electrically interconnected,
wherein said transistor is a thin-film transistor which has an active layer, and a portion of the back-surface electrode is directly connected to said active layer via a contact hole,
wherein said display electrode and said back-surface electrode are patterned into the same shape, and
a thickness of said back-surface electrode is such that no substantial protrusion is formed in said display electrode and said thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å.
The device according to claim 1,
wherein said back-surface electrode is made of a high melting point metal.
3. (Original) The device according to claim 2, wherein
said display electrode is made of aluminum.
4. (Cancelled)
5. (Cancelled)
6. (Currently Amended) The device according to claim 12, wherein said active layer is a polycrystalline silicon layer.
- 7-11. (Cancelled)
12. (Currently Amended) A reflective liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:
a display electrode made of a reflective material for reflecting the incident light on a surface thereof;
a back-surface electrode disposed in contact with a back surface of the display electrode; and
a transistor for controlling current to the display electrode, said back-surface electrode and the transistor being electrically interconnected,

wherein said transistor is a thin-film transistor which has an active layer, and a portion of the back-surface electrode is directly connected to said active layer via a contact hole,

wherein said display electrode and said back-surface electrode are patterned into the same shape, and

a thickness of said back-surface electrode is such that no substantial protrusion is formed in said display electrode and said thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å. The device according to claim 1,

wherein a part of the back-surface electrode elongates to a place above a part of the active layer and the contact hole is formed between the one end portion of the back-surface electrode and the part of the active layer.

13. (Currently Amended) A reflective type liquid crystal display device comprising:
a back-surface electrode layer;
a display electrode layer is constituted of a reflective material on the back-surface electrode layer;

a back-surface electrode layer and the display electrode layer are patterned to form a surface electrode and a back-surface electrode in the same shape;

a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode;

a thin film transistor is formed as an active layer of polycrystalline silicon on a substrate;

an insulating layer is formed to cover the thin film transistor; and
a contact hole is formed in the insulating film, wherein
said back-surface electrode is formed on a smoothened film with said contact hole formed therein, wherein

said back-surface electrode is made of a high melting point metal, and
a thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å.

14. (Currently Amended) A reflective liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:
a display electrode made of a reflective material for reflecting the incident light on a surface thereof;
a back-surface electrode disposed in contact with a back surface of the display electrode; and

a transistor for controlling current to the display electrode, said back-surface electrode and the transistor being electrically interconnected,

wherein said transistor is a thin-film transistor which has an active layer, and a portion of the back-surface electrode is directly connected to said active layer via a contact hole,

wherein said display electrode and said back-surface electrode are patterned into the same shape, and

a thickness of said back-surface electrode is such that no substantial protrusion is formed in said display electrode and said thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1,500 Å. The device according to claim 1,

wherein the back-surface electrode is made of a non-oxide metal.

15. (Previously Presented) The device according to claim 2, wherein
said high melting point metal is selected from the group consisting of molybdenum,
titanium, tungsten, tantalum and chromium, or an alloy thereof.

16-21. (Cancelled)